

| V_{GS} | V_{DS} | Mode | I_{DS} |
|------------|---------------------------------------|---------------------|--|
| $> V_{th}$ | $< V_{GS} - V_{th}$ | Resistive | $\mu_n C_{OX} \left(\frac{W}{L}\right) \left((V_{GS} - V_{th}) V_{DS} - \frac{(V_{DS})^2}{2} \right)$ |
| | $> V_{GS} - V_{th}$ & $< V_{DSAT}$ | Saturation | $\frac{\mu_n C_{OX}}{2} \left(\frac{W}{L}\right) (V_{GS} - V_{th})^2$ |
| | $> V_{DSAT}$ | Velocity Saturation | $\nu_{sat} C_{OX} W \left(V_{GS} - V_{th} - \frac{V_{DSAT}}{2} \right)$ |
| $< V_{th}$ | | Subthreshold | $I_S \left(\frac{W}{L}\right) e^{\frac{V_{GS} - V_{th}}{nkT/q}}$ |

1. Consider an NMOS transistor with $L_{eff}=25\text{nm}$ and $V_{ds}=1\text{V}$

(a) What is the electrical field (F) in $\text{V}/\mu\text{m}$ in the channel between source and drain?

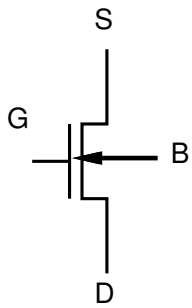
$(F = V/L)$

(b) With an electron mobility of $\mu_n=500 \text{ cm}^2/(\text{V} \cdot \text{s})$, what is the velocity of the electron in this field? (in m/s)?

(velocity $v = \mu \times F$)

(c) At what V_{ds} voltage does the velocity reach 10^5 m/s ?

2. How many capacitance values might we need to represent a 4-terminal transistor?
 (fourth terminal is body)

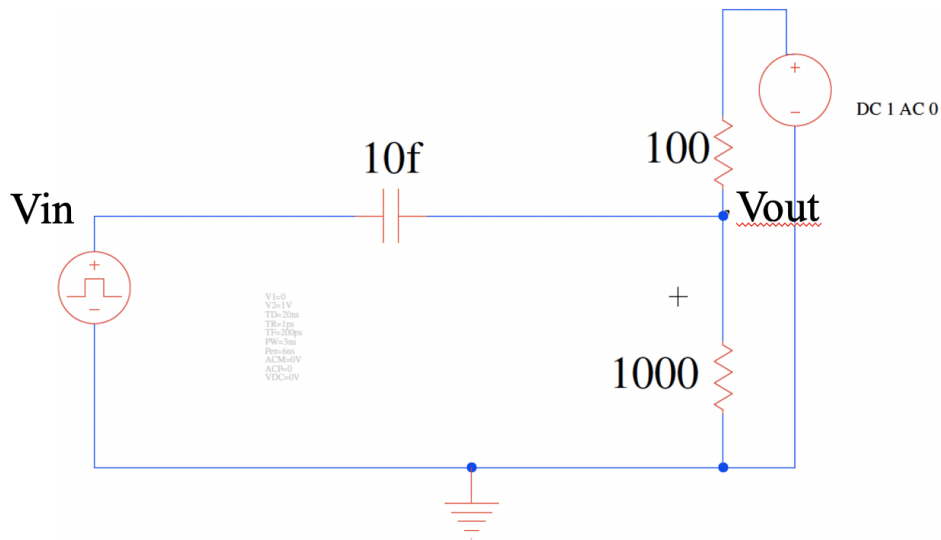


Hint: How many terminal pairs are there?

| Terminal Pair | Capacitance |
|---------------|-------------|
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Use in class for notes to summarize cases and capacitances.

3. Assuming a step input from 0 to 1V by the pulse generator on the left, what does the voltage on V_{out} as a function of time look like?



Hints: What is the initial voltage? What is the steady-state voltage as $t \rightarrow \infty$?